

1-Line Bidirectional ESD Protection Diode

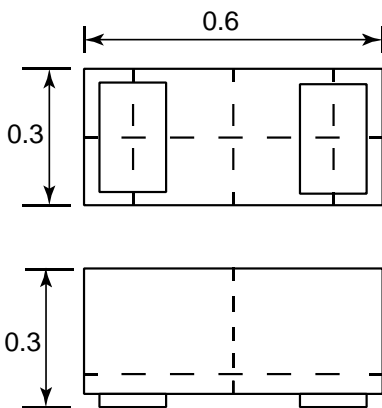
Description

The PESDR3311P0 is an uni-directional TVS diode, to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The PESDR3311P0 has an ultra-low capacitance with a typical value at 0.45pF, and complies with the IEC61000-4-2 (ESD) standard with ±20kV air and ±15kV contact discharge. It is assembled into an ultra-small 0.6x0.3x0.3mm lead-free DFN package. The small size, ultra-low capacitance and high ESD surge protection make PESDR3311P0 an ideal choice to protect cellphone, digital video interfaces, HDMI, DVI, USB2.0, USB3.0 and other high speed ports.

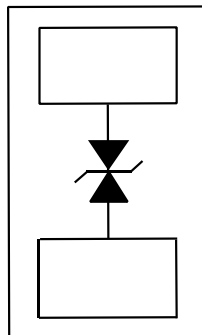
Features

- Ultra small package: 0.6x0.3x0.3mm
- Very low capacitance
- Protects one data or power line
- Ultra low leakage: nA level
- Operating voltage: 3.3V
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: ±20kV
 - Contact discharge: ±15kV
 - IEC61000-4-5 (Lightning) 4A (8/20µs)
- RoHS Compliant

Dimensions and Pin Configuration



Package Dimensions



Circuit and Pin Schematic

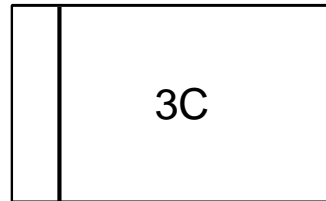
Mechanical Characteristics

- Package: DFN0603-2 (0.6x0.3x0.3mm)
- Case Material: “Green” Molding Compound.
- Moisture Sensitivity: Level 1 per J-STD-020
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Display Ports
- MDDI Ports
- USB Ports
- Digital Video Interface (DVI)
- PCI Express and Serial SATA Ports

Marking Information



3C = Device Marking Code

Ordering Information

Part Number	Shipping	Reel Size
PESDR3311P0	10000/Tape & Reel	7 inch

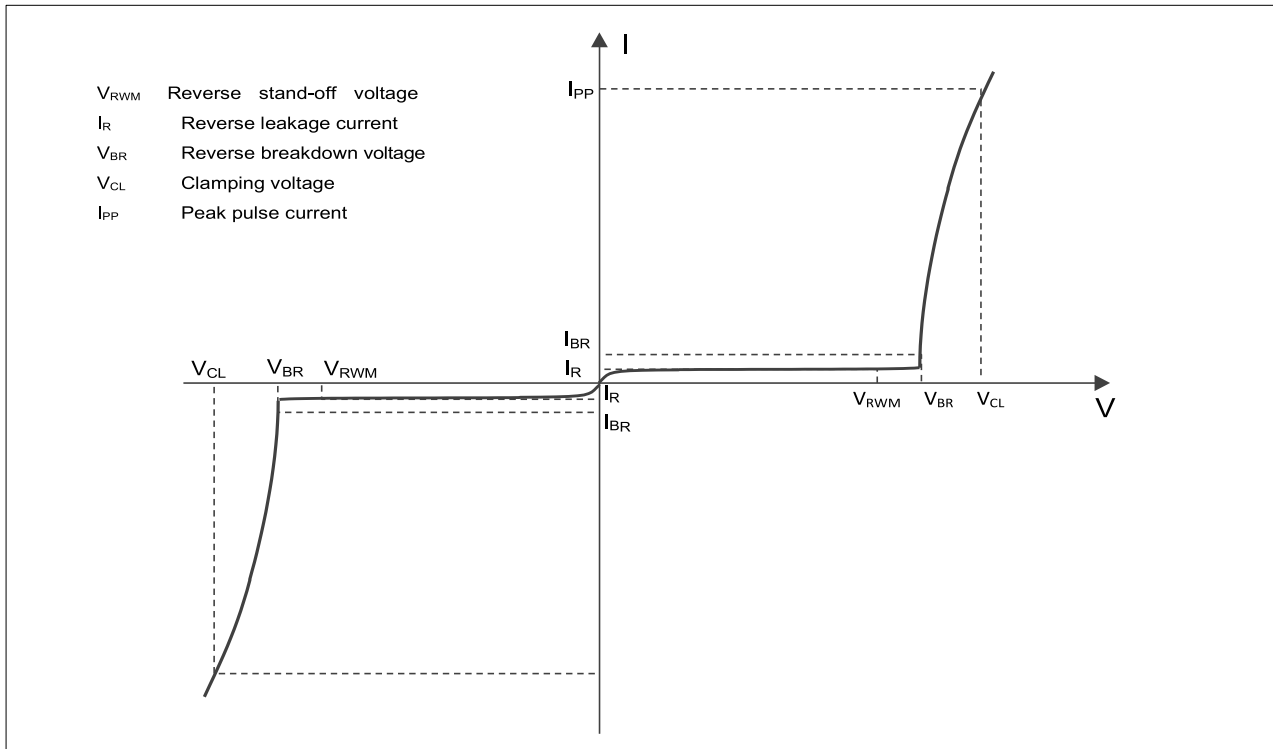
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	P _{PK}	100	W
Peak Pulse Current (8/20μs)	I _{PP}	4	A
ESD per IEC 61000-4-2 (Air)	V _{ESD}	±20	kV
ESD per IEC 61000-4-2 (Contact)		±15	
Lead temperature	T _L	260	°C
Operating Temperature Range	T _{OP}	-40 ~ +85	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

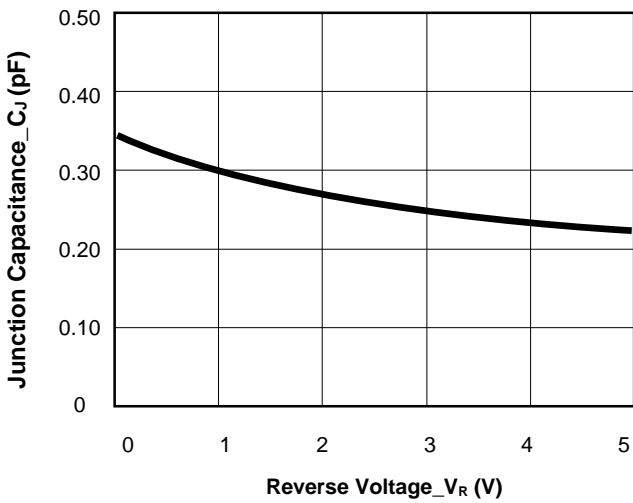
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			3.3	V	
Breakdown Voltage	V _{BR}	5.0	6.0	8.0	V	I _T = 1mA
Reverse Leakage Current	I _R			0.2	μA	V _{RWM} = 3.3V
Clamping Voltage ³⁾	V _C			11	V	I _{PP} = 1A(8/20μs pulse)
Clamping Voltage ³⁾	V _C			25	V	I _{PP} = 4A(8/20μs pulse)
Junction Capacitance	C _J		0.35		pF	V _R = 0V, f = 1MHz

Electrical characteristics ($T_A = 25^\circ\text{C}$, unless otherwise noted)

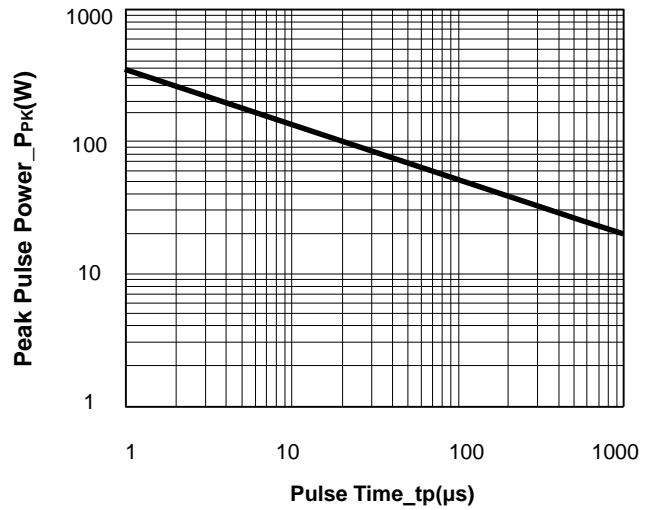


Definitions of electrical characteristics

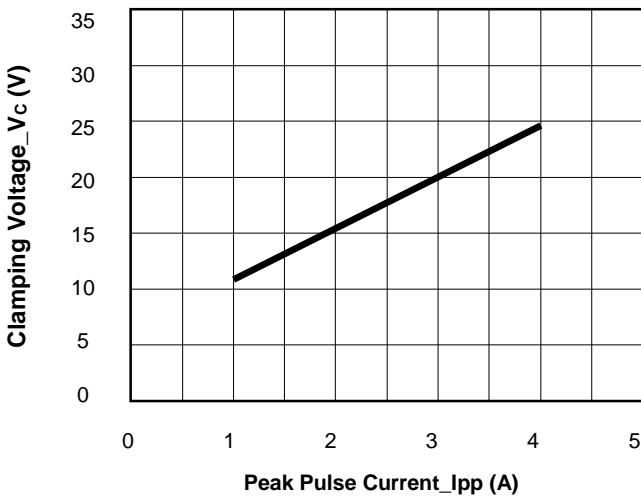
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



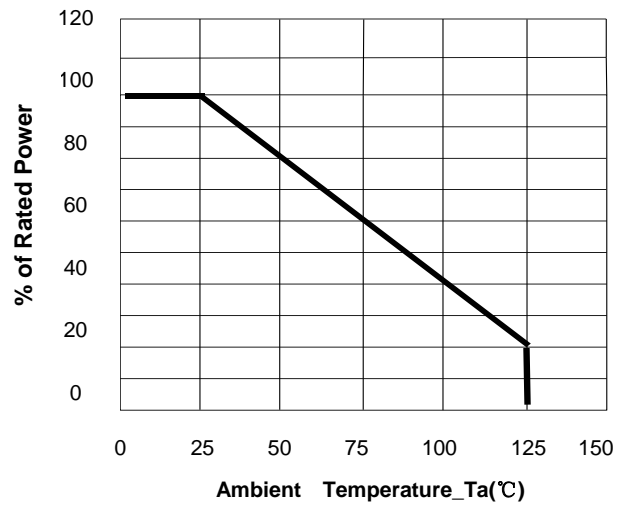
Junction Capacitance vs. Reverse Voltage



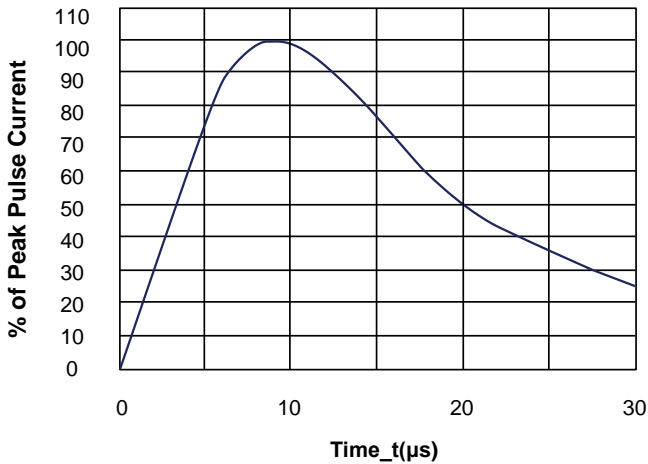
Peak Pulse Power vs. Pulse Time



Clamping Voltage vs. Peak Pulse Current

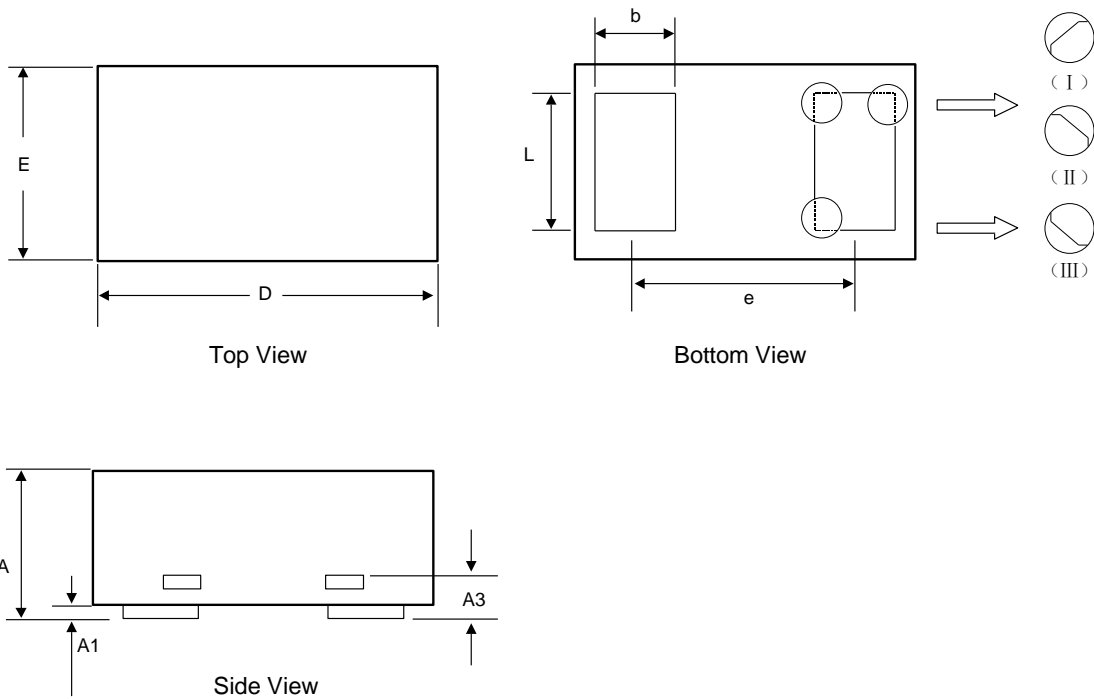


Power Derating Curve



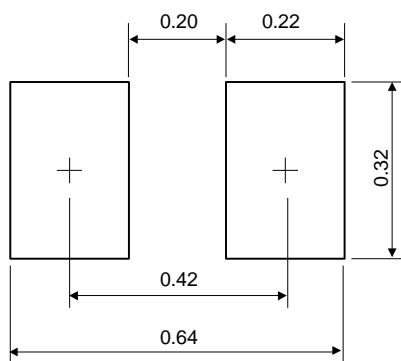
8/20μs Pulse Waveform

DFN0603-2 Package Outline Drawing



Symbol	Dimensions in Millimeters		
	Min.	Typ.	Max.
A	0.230	0.300	0.350
A1	0.000	-	0.050
A3	0.102REF.		
D	0.550	0.600	0.670
E	0.250	0.300	0.370
b	0.160	0.190	0.230
L	0.215	0.245	0.275
e	0.360 BSC		

Recommended PCB Layout (Unit: mm)

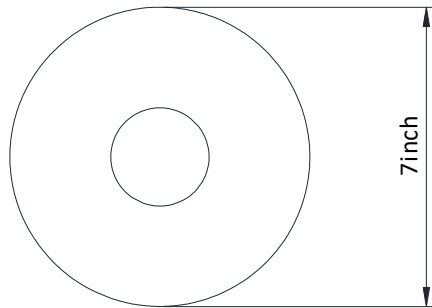


Notes:

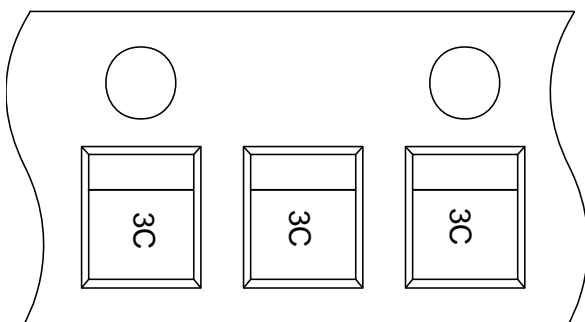
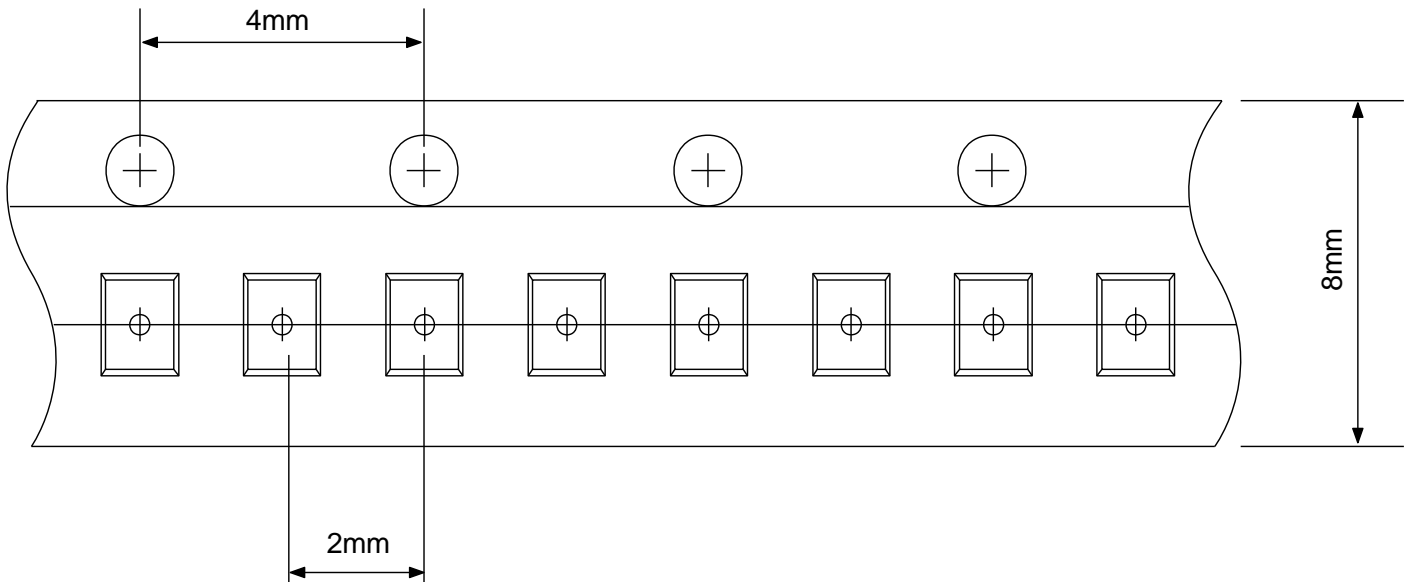
This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

TAPE AND REEL INFORMATION

Reel Dimensions



Tape Dimensions




User Direction of Feed

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